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RELIABILITY OF WIDE-BANDGAP POWER ELECTRONICS: DEVICES TO SYSTEMS

Presentation ID 902

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ACKNOWLEDGEMENT

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PE RELIABILITY PROGRAM HISTORICAL HIGHLIGHTS

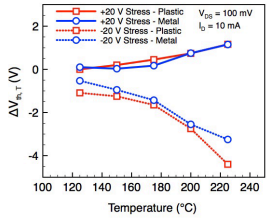
2009

2024

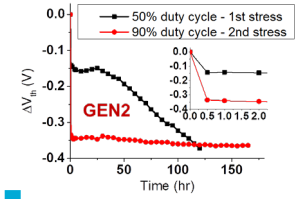
Suggested reliability improvements for components, software, and operation of Silicon Power Corporation's Solid-State Current Limiter

Developed and documented a general process for analyzing the reliability of any power electronics system

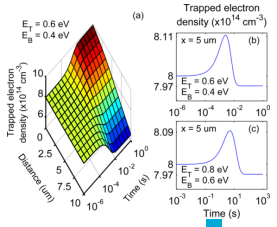
Characterized and evaluated commercial SiC MOSFETs, including the impacts of bias, temperature, packaging, and AC gate stress on reliability



Developed models for SiC threshold voltage instability, and identified the free-wheeling diode ideality factor as a potential screening metric for threshold voltage shifts



Created a physics-based model for GaN HEMTs linking defect properties to device design

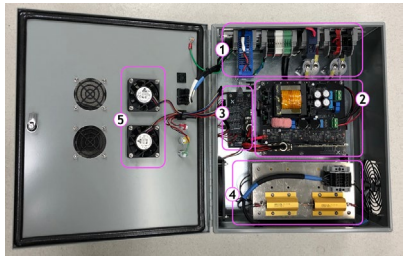


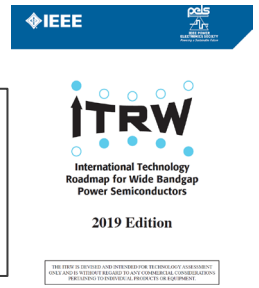
Developed an easy to use method that can be used by circuit designers to evaluate the reliability of commercial SiC MOSFETs

Characterized switching of vertical GaN PiN diodes using double-pulse test circuit

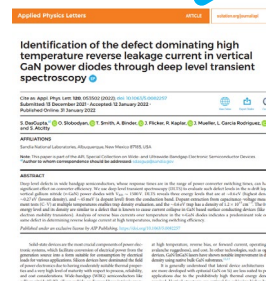
Participated in JEDEC WBG reliability working group

Constructed half-bridge hard-switching test circuit



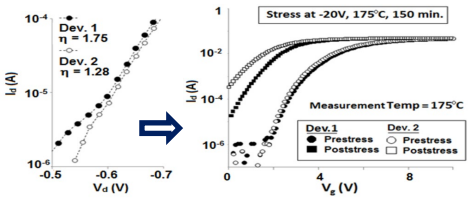


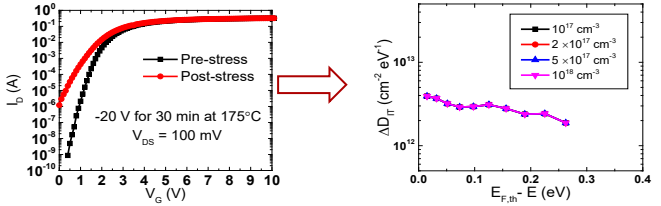
Led ITRW materials and devices working group



Applied Physics Letters journal article on defects in GaN selected as Editor's Pick

Over 30 papers and presentations over the course of the project

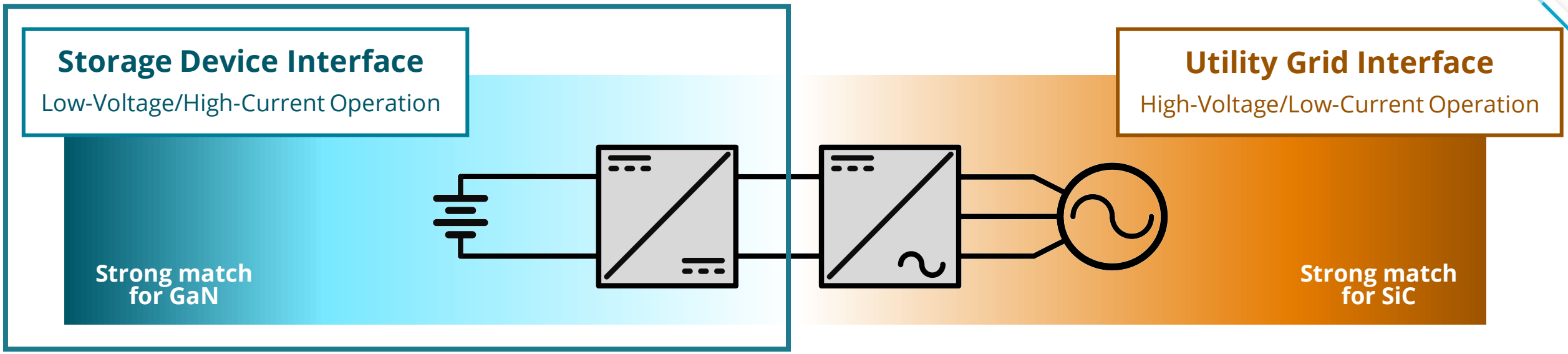




Serving as an unbiased evaluator of reliability to the WBG power electronics community, ranging from static device testing to in-circuit dynamic evaluation

PROJECT MOTIVATION AND GOALS

GaN results discussed in first part of presentation



Power conversion system operating requirements are diverse – no single technology serves all needs.

All candidate solutions must provide exceptionally high reliability.

Program Goals: **Identify semiconductor technologies best suited to all needs of energy storage**

Understand device performance and reliability in realistic operating conditions

Evaluate new devices' circuit- and system-level impact potential

PRIOR WORK: REPETITIVE DOUBLE-PULSE TESTING

Mission-Profile Based Reliability

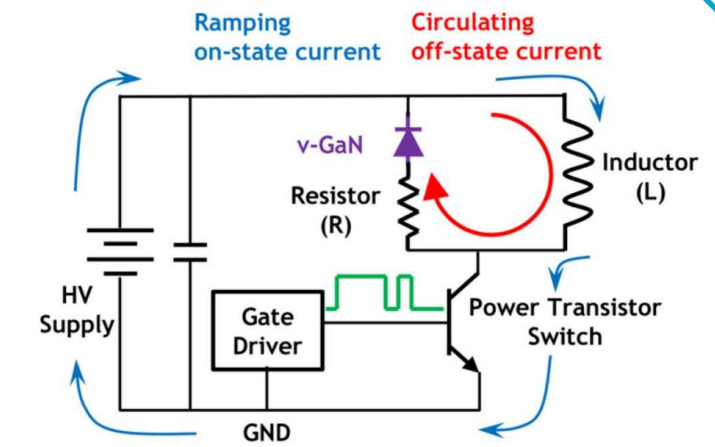
- Device reliability is influenced by its mission profile, which includes specific operating parameters and environmental stressors.

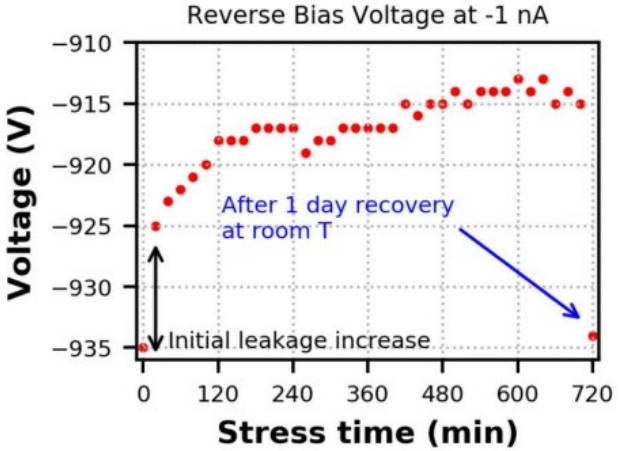
Value of Data from Practical Application Testing

- Translates device-level characterization to system-level performance improvements.
- Provides immediate utility for system integration, design optimization, and better monitoring of device and system integrity.
- Enhances lifetime estimates and maintenance scheduling.

Repetitive double-pulse testing (RDPT)

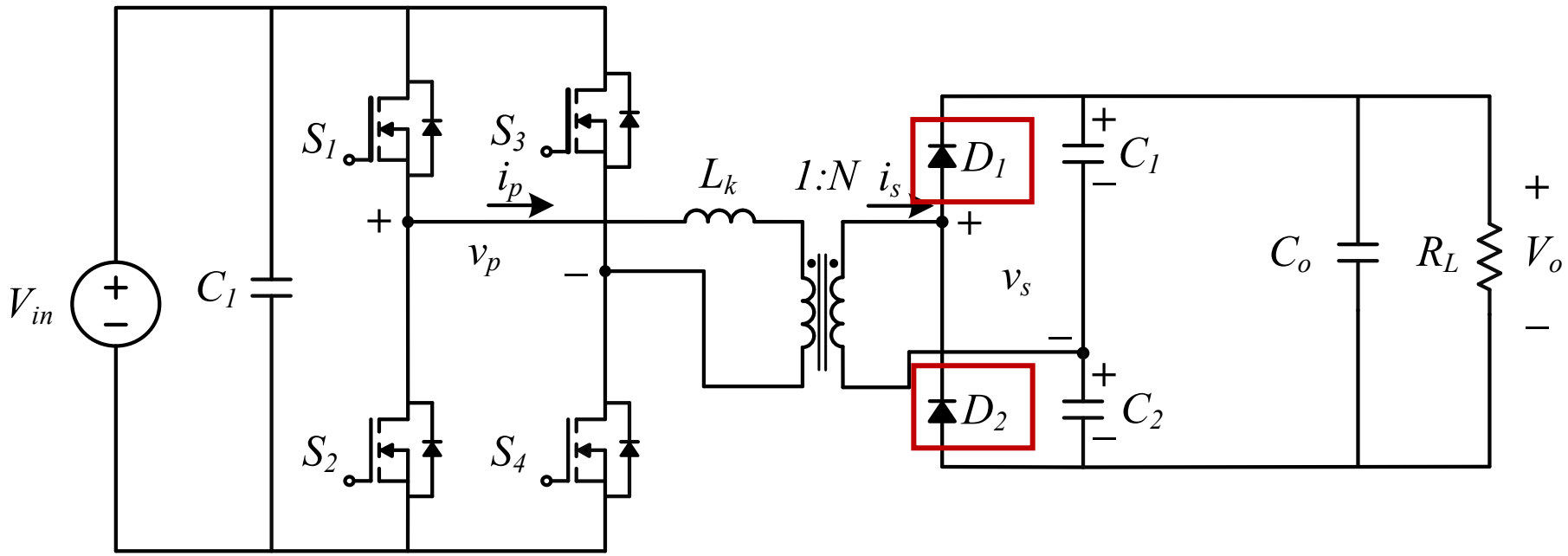
- RDPT simplifies mission profile emulation for various technologies but cannot fully replicate real-world conditions.
- Vertical GaN diodes were stressed in 20 min intervals. The reverse and forward I/V characteristics were measured using a Keysight B1505 Power Device Analyzer.
- Experiments were performed for a total of 720 min at 500, 750, and 1000 V with 0.2% duty cycle.





Slobodyan, O., Smith, T., Flicker, Jack, Sandoval, S., Matthews, C., Heukelom, M., Kaplar, R., & Atcitty, Stan. (2018). Hard-switching reliability studies of 1200 V vertical GaN PiN diodes. MRS Communications. 8. 1-5. 10.1557/mrc.2018.204.

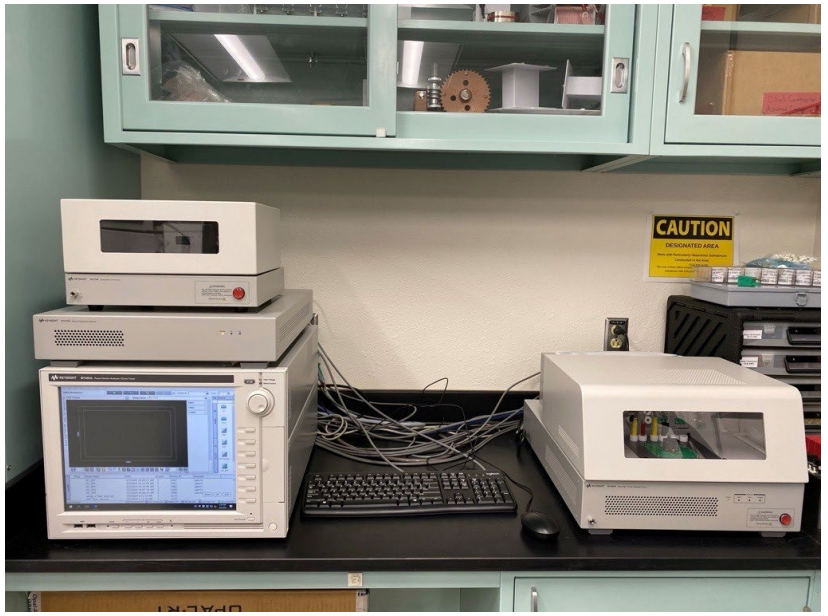
FULL-BRIDGE VOLTAGE DOUBLER CONVERTER TOPOLOGY



Method can be applied generally to new WBG technologies

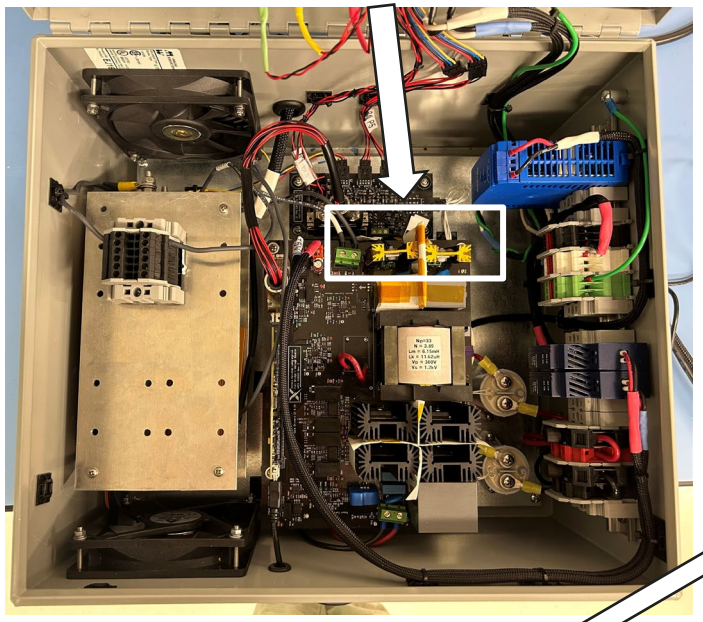
- The Full-Bridge Voltage Doubler (FBVD) converter was designed and built to stress the v-GaN diodes under practical circuit conditions.
- The FBVD provides a reverse bias voltage across the diodes that is predictable and absent of high-frequency voltage disturbances.
- More than 3 dozen sample pairs of v-GaN diodes were stressed at 500, 700, and 900 V with an average current of 1 A using the FBVD converter operating at 100 kHz.
- After 1 hr of converter operation, the diodes were removed from the circuit and the reverse and forward I/V curves were extracted. The total stress process was set to 6 hrs for each diode pair.

EXPERIMENTAL SETUP



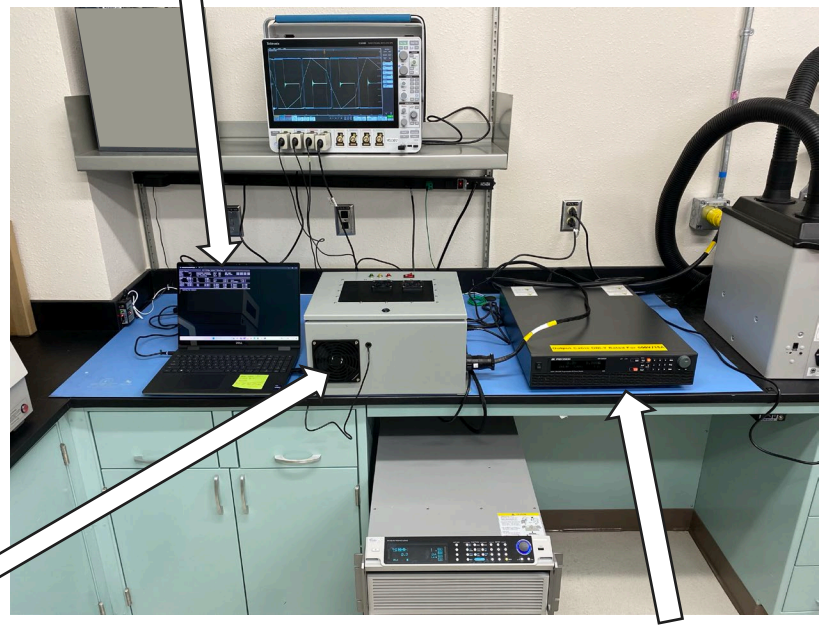
B1505 Power Device Analyzer Setup

Devices under test D_1 and D_2



Safety Enclosure

Comms/Data Logging

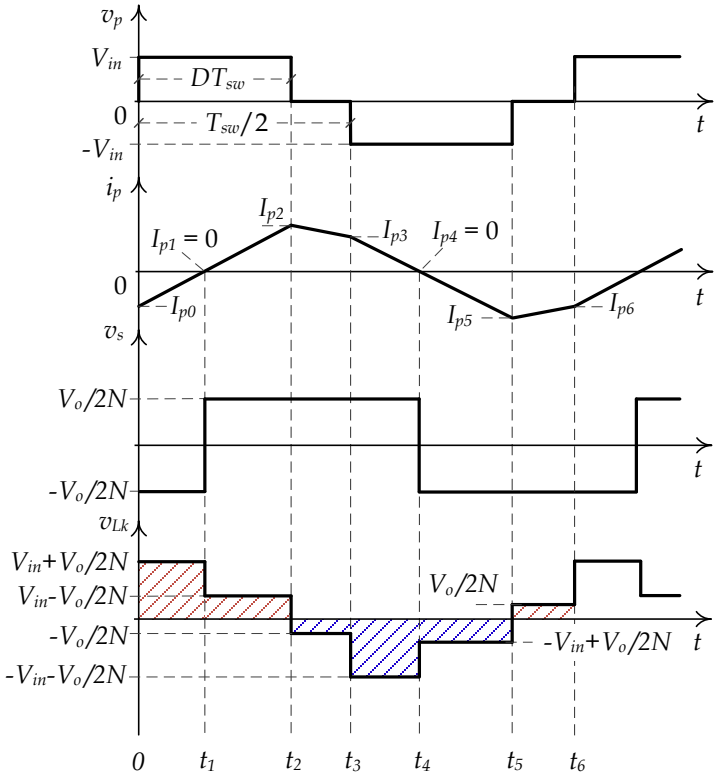


Electronic Load

DC Power Supply

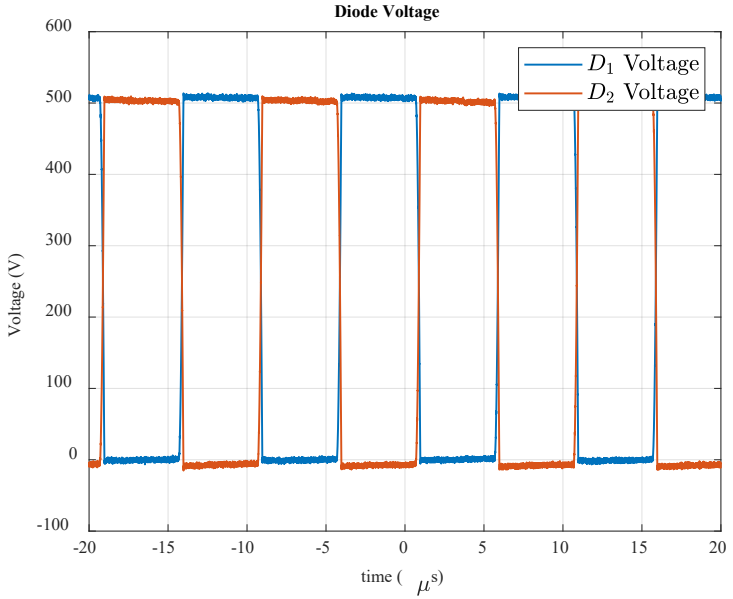
- The reliability/stress testing of the v-GaN diodes is done within the custom-built safety enclosure, which has multiple layers of protection for the device and user.
- The safety enclosure is inserted into the larger test setup that consists of a DC power supply, electronic load, oscilloscope, laptop, and B1505 power device analyzer.

DIODE IN-CIRCUIT STRESS WAVEFORMS



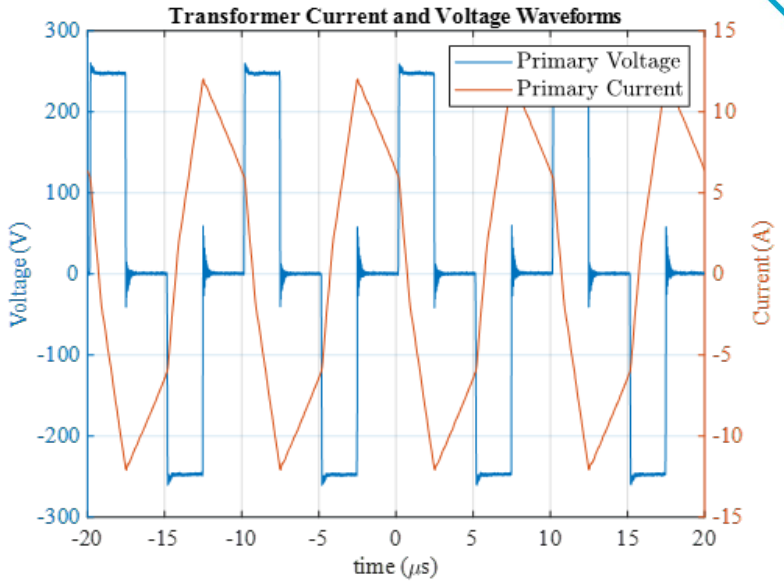
Time interval breakdown

- Theoretical waveforms showing the operation of the circuit in CC mode.



In-circuit measured diode waveforms

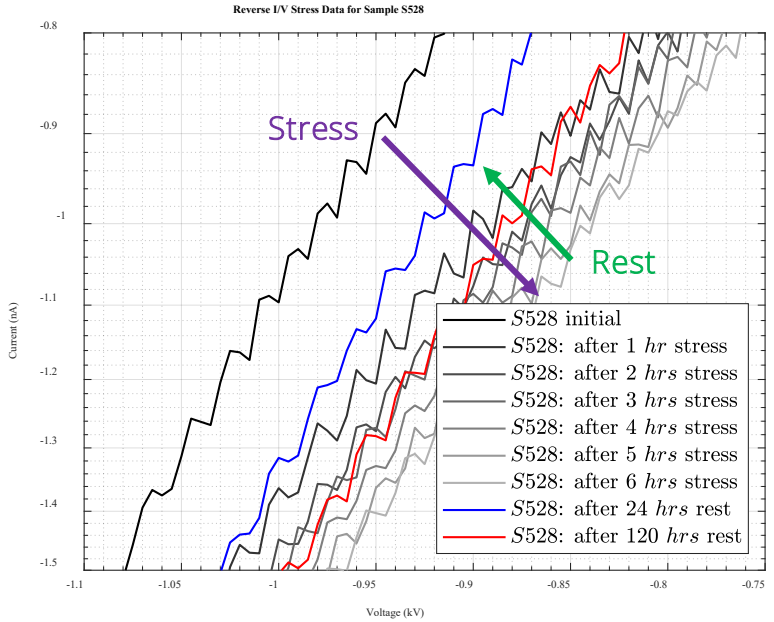
- Voltage waveforms captured for the 500 V stress test of D_1 and D_2.

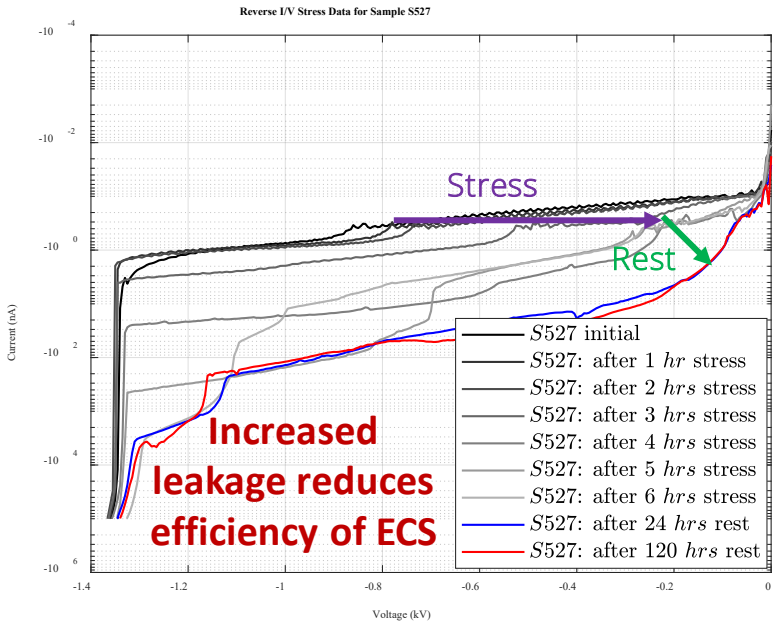


Transformer primary voltage and current waveforms

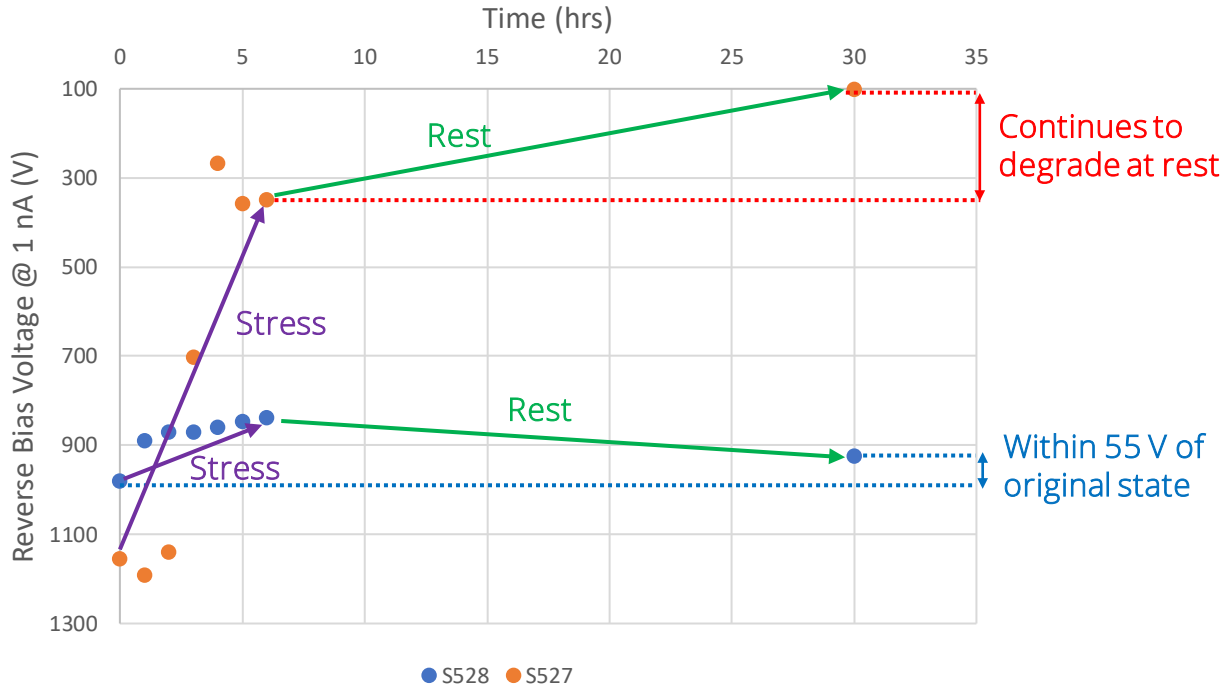
- Transformer current shows proper CC mode of operation for the 500 V stress test.

RESULTS FROM REVERSE I/V CURVES AFTER 6 HRS STRESS

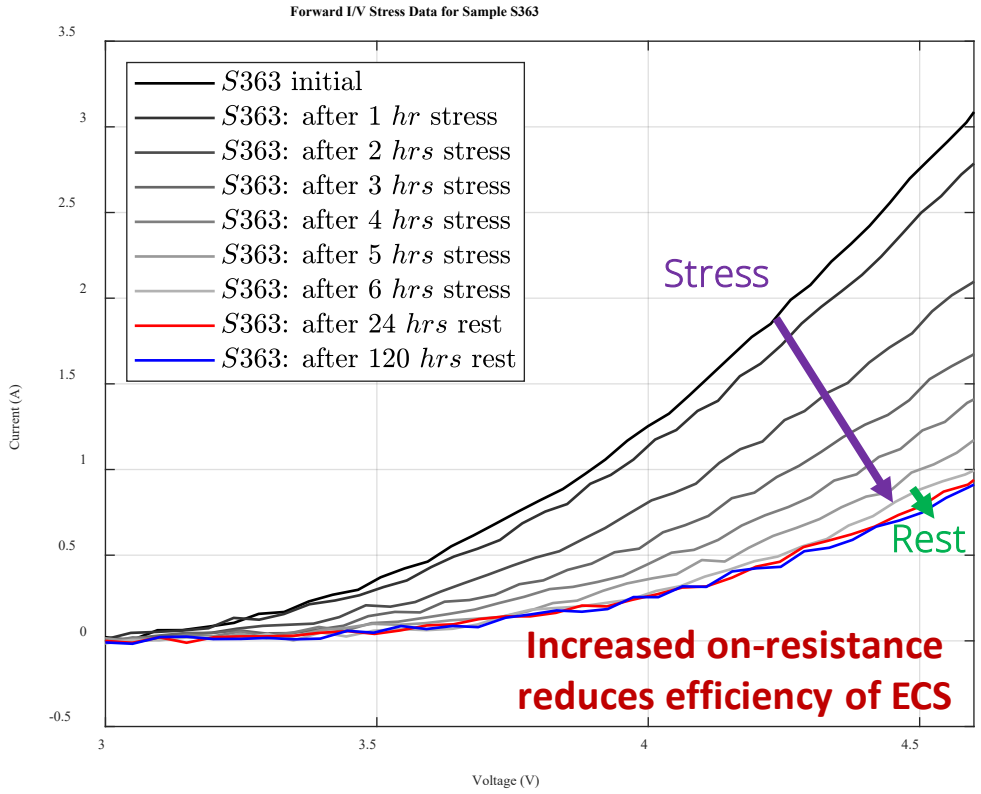


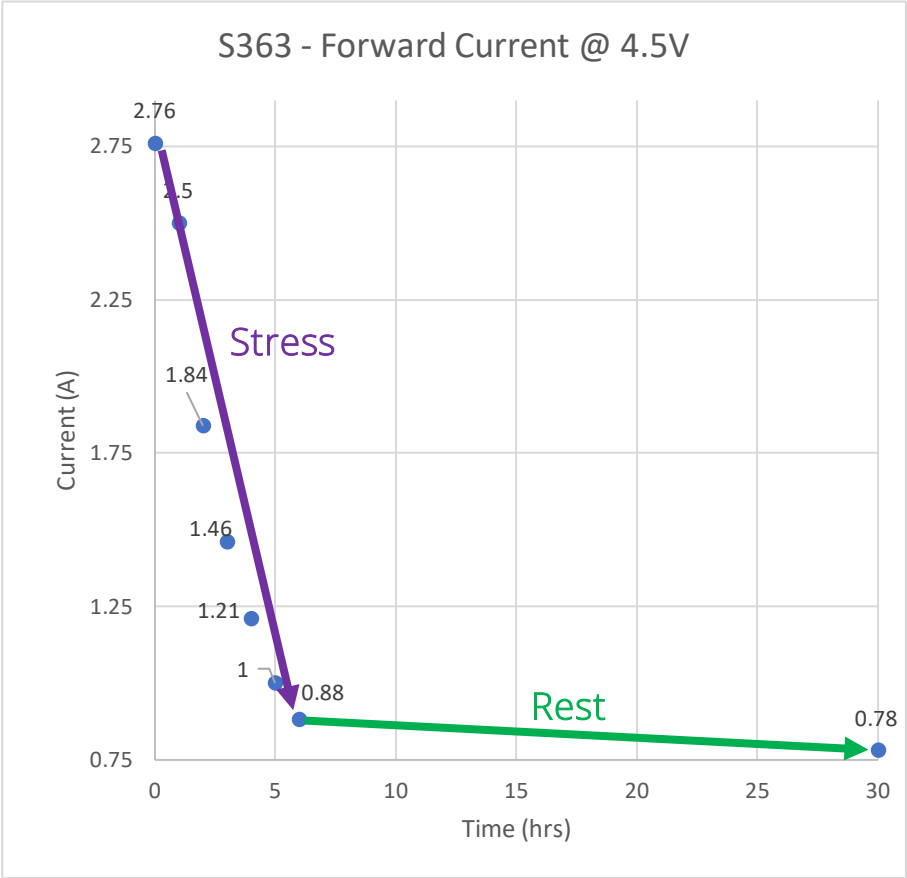


- The previous RDPT experimental results where the v-GaN diodes showed degradation and recovery after rest were replicated in some, although not all, of the tests.
- Other v-GaN devices showed major degradation during stress, and kept degrading even after rest.
- The two different behaviors could be due to process variations, and the test can potentially be used as a screen to identity devices that may perform poorly in a power converter.



RESULTS FROM FORWARD I/V CURVES AFTER 6 HRS STRESS





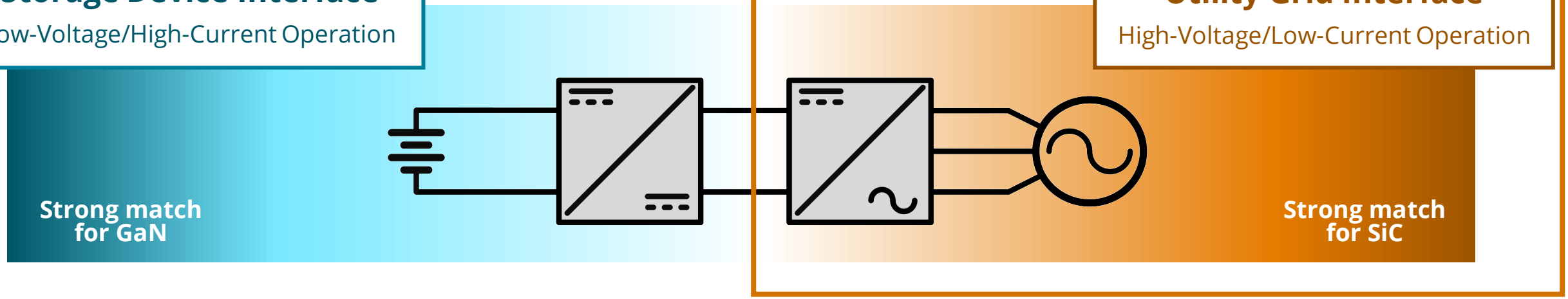
- The forward characterization showed that the devices did not recover even when the reverse characterization of the device showed some recovery, and in some cases the degradation continued even during rest.
- This result was consistent throughout every voltage level in every pair of diodes that were tested.
- Suggests a different root cause than for the reverse-bias degradation, probably not related to charge trapping due to lack of recovery after stress.

SIC MOSFET STRESS TESTING

SiC results discussed in second part of presentation

Storage Device Interface
Low-Voltage/High-Current Operation

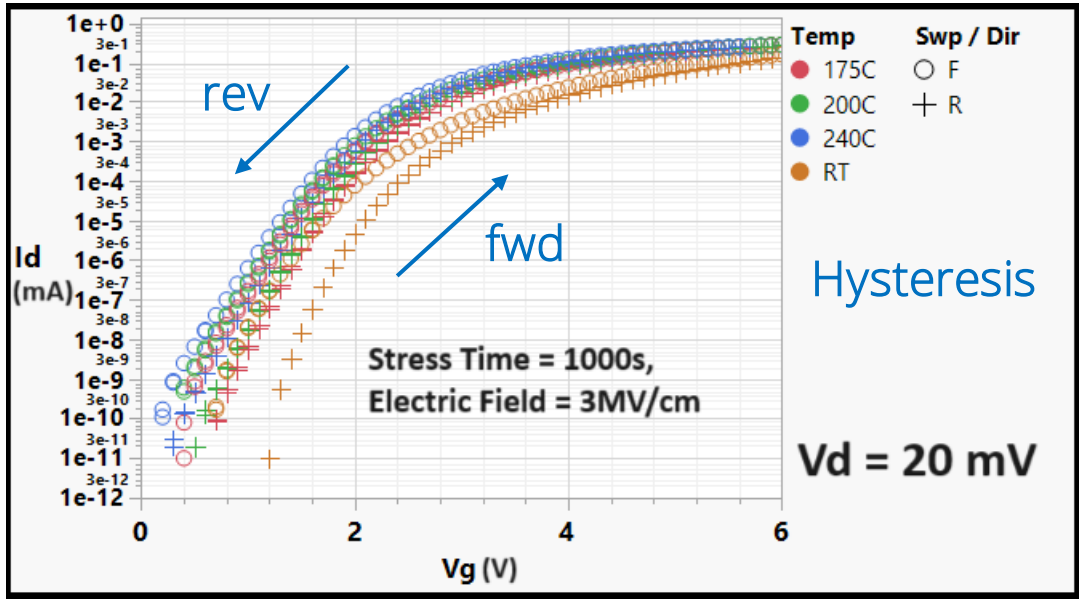
Utility Grid Interface
High-Voltage/Low-Current Operation

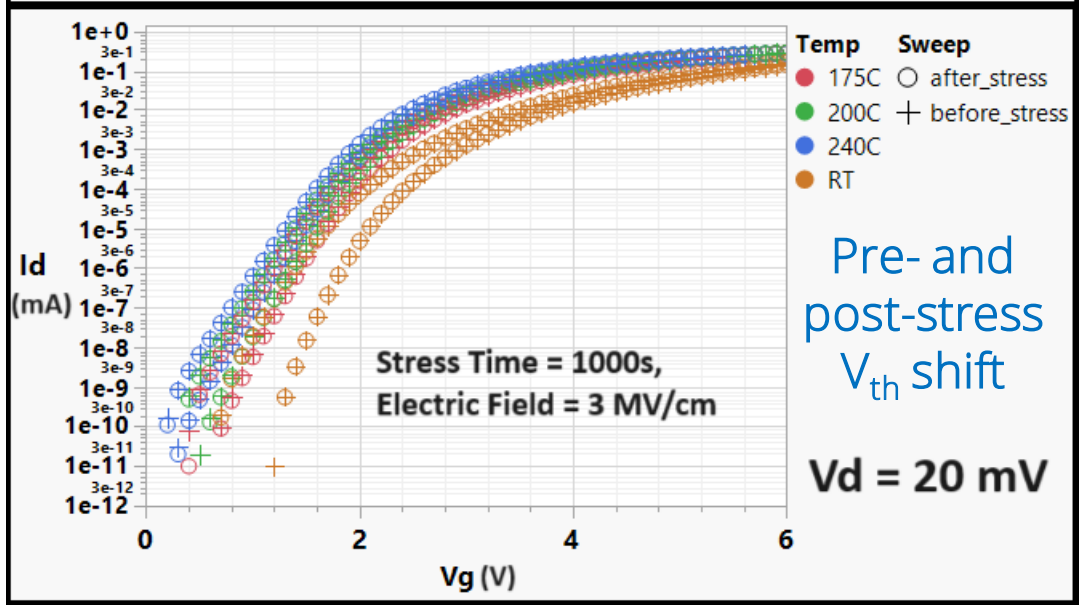


- **GaN is a strong match for the low-voltage/high-current requirements at the battery interface, motivating the studies just described.**
- **SiC is well-matched to the high-voltage/low-current grid interface, with gate oxide integrity being the main degradation factor for SiC MOSFETs.**
- **This motivates our present work on bias-temperature stability evaluation and comparison between old and new generations of SiC MOSFETs – *shifts in device parameters can adversely impact operation of the power converter.***

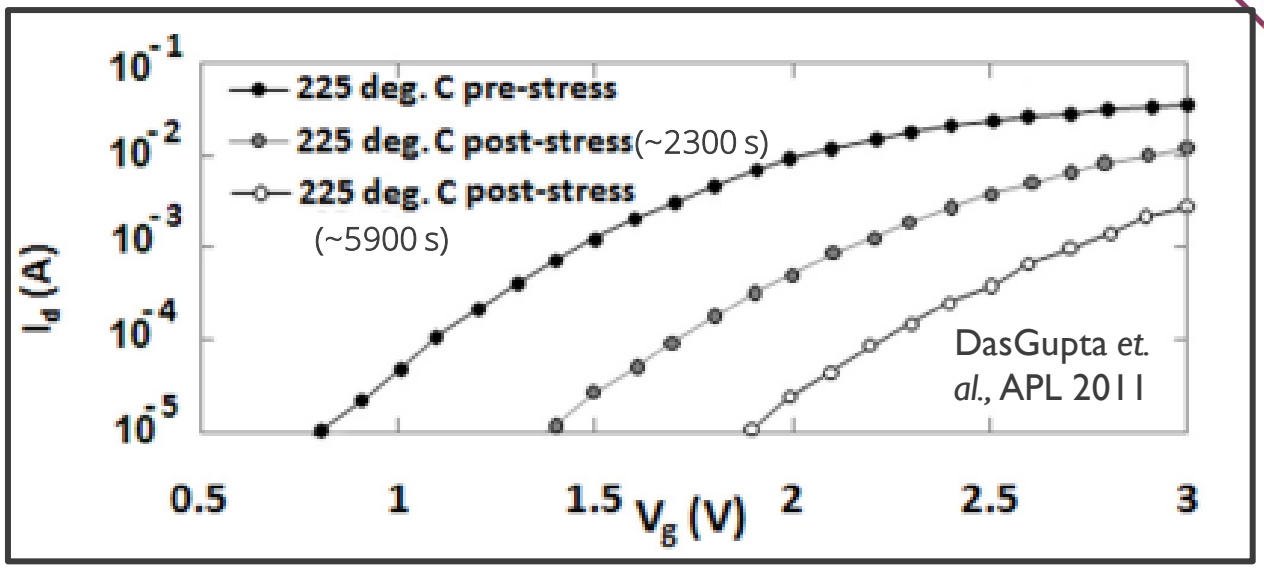
SIC MOSFET BIAS-TEMPERATURE STRESS DATA

Present Generation



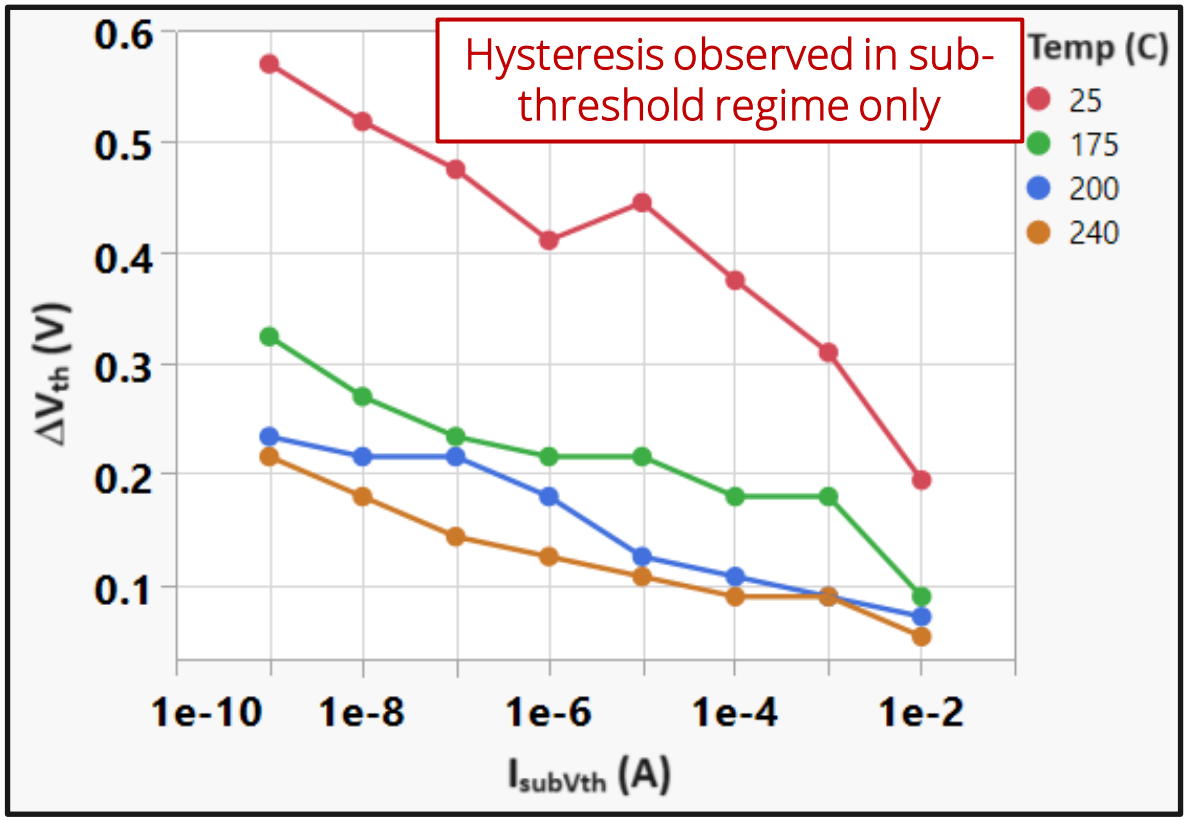


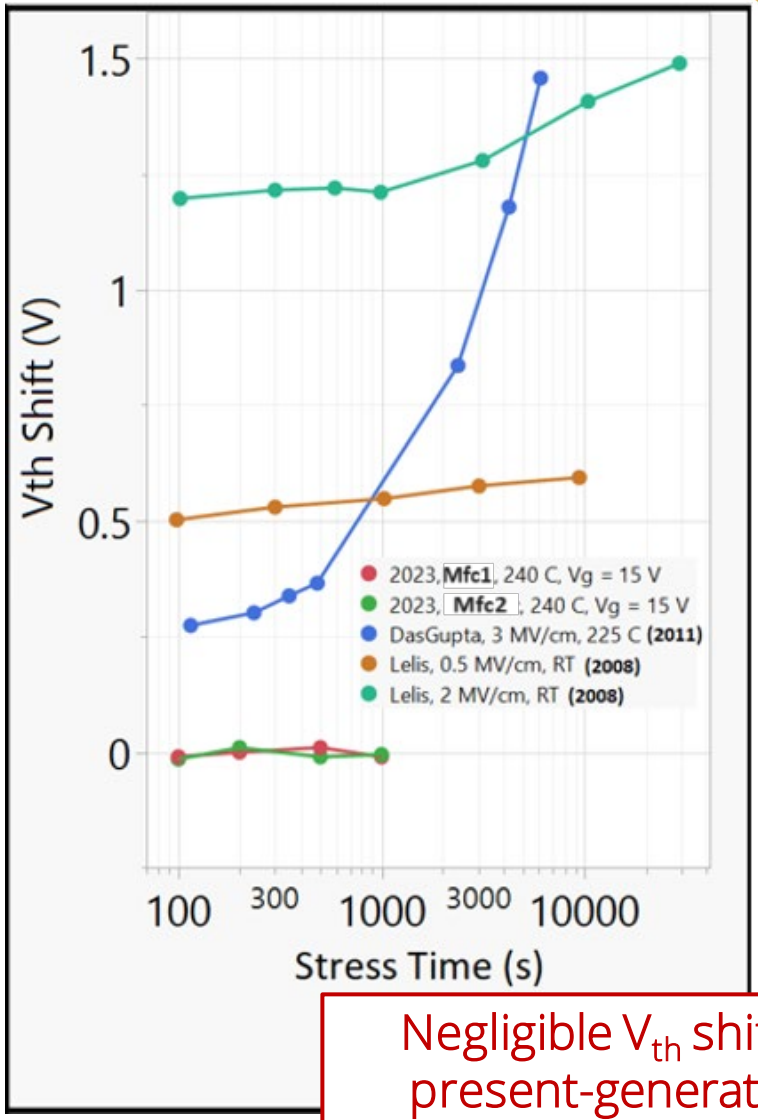
1st Generation



- 1st generation of SiC MOSFETs with SiO_2 gate oxide showed monotonic V_{th} shift with stress.
  - Started at ~150°C and increased with temperature and DC stress time.
  - V_{th} shift was ~0.7 V at 225°C after 1000 s of stress.
  - The shift was ~0.6 V from oxide trapping and ~0.1 V from interface trapping.
- Present MOSFETs show *no V_{th} shift or drive current loss up to 240°C.*
- However, *they exhibit a pronounced hysteresis*, which is larger at low temperature and reduces with increasing temperature.

1ST-GENERATION VS PRESENT-GENERATION OXIDES: HYSTERESIS VS STRESS-INDUCED VTH SHIFTS





- Hysteresis in present-generation MOSFETs is ~0.6 V at low current, ~0.2 V near V_{th} at room temperature, *decreases with temperature* reducing to ~0.2 V at low current, and ~0.05 V near V_{th} at 240°C.
- V_{th} shift in 1st-generation oxides was ~0.7 V at 225°C, 1000 s stress.
- The subthreshold swing is comparable in the 2 generations.

Therefore, overall bias-temperature instability is improved at high temperature and degraded at low temperature in present-generation SiC MOSFETs

Negligible V_{th} shift in present-generation MOSFETs compared to 1st generation

1ST-GENERATION VS PRESENT-GENERATION OXIDES: HYSTERESIS VS V_{TH} SHIFT SUMMARY TABLE

Feature	1st Generation	Present Generation
Oxide trapping, Vth/drive current shift	Monotonic, starts at 150°C, increases with temperature and stress time, Vth shift is ~0.6 V at 225°C and 1000 s stress	None up to 240°C
Interface trapping, Vth/drive current shift	Monotonic, starts at 150°C, increases with temperature and stress time, Vth shift is ~0.1 V at 225°C and 1000 s stress	None up to 240°C
Hysteresis	None	~0.6 V at low current, ~0.2 V near Vth at room temperature, *decreasing with temperature* and reducing to ~0.2 V at low current and ~0.05 V near Vth at 240°C
Sub Vth Swing	kT/q + ~180 mV from interface traps (~2 orders of magnitude below threshold current)	kT/q + ~180 mV from interface traps (~2 orders of magnitude below threshold current)

HYSTERESIS IN PRESENT-GENERATION MOSFETS: POSSIBLE MECHANISM

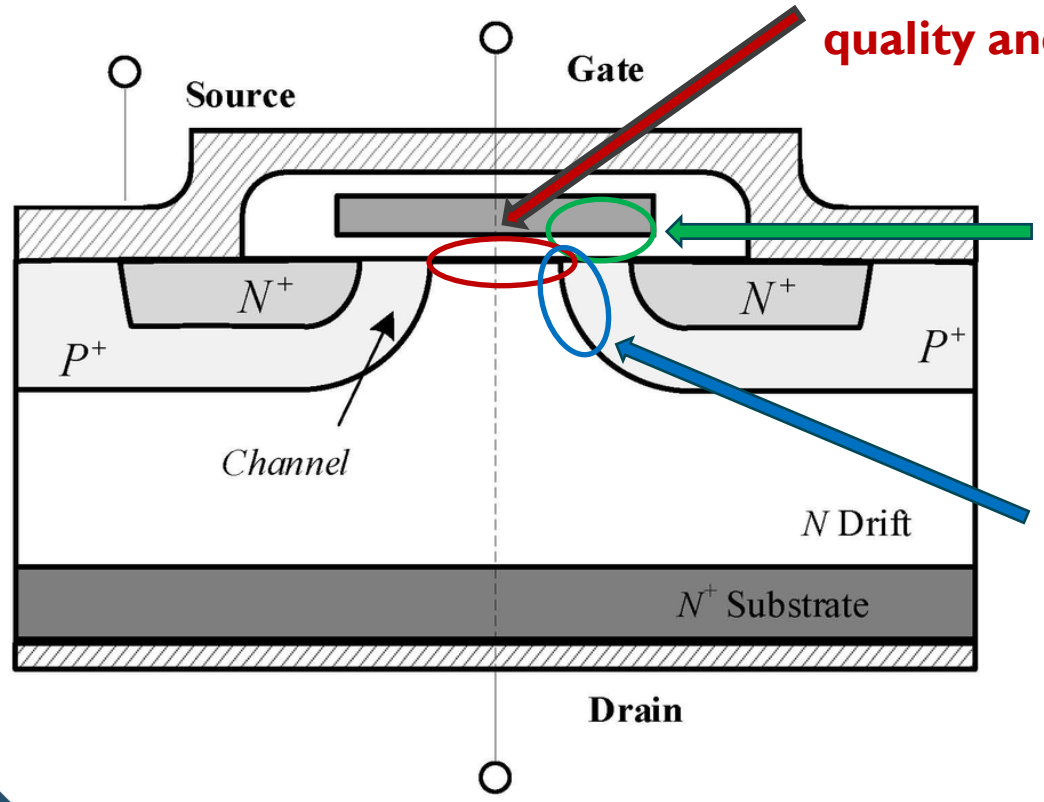
Shifts in device parameters can adversely impact operation of the power converter

Key Observations:

i) No change in drive current; *change is entirely in the subthreshold conduction regime.*

ii) Hysteresis is high at low temperature, reduces at high temperature.

Both observations are more suggestive of a floating body effect rather than trapping in the oxide over the channel



MOSFETs have higher electron density and *might have* poor oxide quality and coverage in the n-region away from channel

Lower e density, better coverage and quality in channel, no trapping, no change to drive current

In body-drift junction near dielectric, body potential shift could lead to change in subthreshold current

Subthreshold current $I_D = I_{D0}e^{VGS/kT}$

$I_{D,\ pre\ trapping} = I_{D0}e^{VGS/kT}$

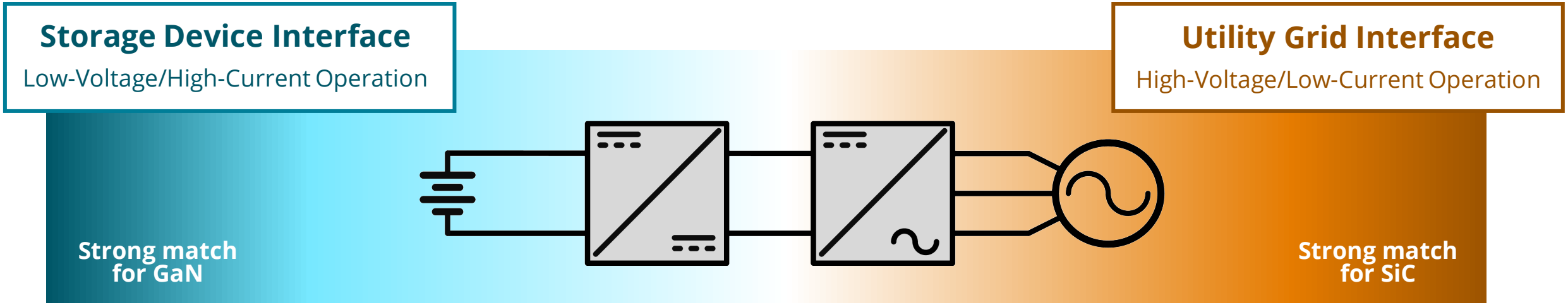
$I_{D,\ post\ trapping} = I_{D0}e^{(VGS\ -\ \Delta Vtrap)/kT}$

$$I_{D,\ pre\ trapping}/I_{D,\ post\ trapping} = e^{\Delta Vtrap/kT}$$

Indicates that subthreshold conduction degradation reduces with increasing temperature, consistent with observations

CONCLUSIONS

- **Using a GaN diode and SiC MOSFET exemplar cases, we have established a process that allows us to evaluate new WBG device technologies using electrical characterization data and switching characteristics in representative circuits.**
- **This process provides a resource for the ES community to understand the performance, reliability, and overall potential of new WBG technologies based on unbiased third party testing.**
- **This process of preliminary validation of new WBG technologies is crucial to the power electronics connected to ESS, which can optimally make use of both GaN for low-voltage/high-current needs and SiC for high-voltage/low-current needs.**



Questions?

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